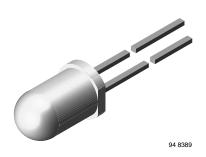
GREEN

<u>(5-2008)</u>**



Vishay Semiconductors

High Speed Infrared Emitting Diode, 850 nm, GaAlAs Double Hetero



DESCRIPTION

TSHG6210 is an infrared, 850 nm emitting diode in GaAlAs double hetero (DH) technology with high radiant power and high speed, molded in a clear, untinted plastic package.

FEATURES

Package type: leadedPackage form: T-1¾

• Dimensions (in mm): Ø 5

Peak wavelength: λ_p = 850 nm

· High reliability

· High radiant power

• High radiant intensity

• Angle of half intensity: $\phi = \pm 10^{\circ}$

· Low forward voltage

· Suitable for high pulse current operation

• High modulation bandwidth: f_c = 18 MHz

· Good spectral matching with CMOS cameras

 Compliant to RoHS Directive 2002/95/EC and in accordance to WEEE 2002/96/EC

APPLICATIONS

- Infrared radiation source for operation with CMOS cameras
- High speed IR data transmission
- Smoke-automatic fire detectors

PRODUCT SUMMARY					
COMPONENT	I _e (mW/sr)	φ (deg)	$φ$ (deg) $λ_p$ (nm)		
TSHG6210	230	± 10	850	20	

Note

• Test conditions see table "Basic Characteristics"

ORDERING INFORMATION					
ORDERING CODE	PACKAGING	REMARKS	PACKAGE FORM		
TSHG6210	Bulk	MOQ: 4000 pcs, 4000 pcs/bulk	T-1¾		

Note

· MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS (T _{amb} = 25 °C, unless otherwise specified)					
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT	
Reverse voltage		V_R	5	V	
Forward current		I _F	100	mA	
Peak forward current	$t_p/T = 0.5$, $t_p = 100 \mu s$	I _{FM}	200	mA	
Surge forward current	t _p = 100 μs	I _{FSM}	1	Α	
Power dissipation		P _V	180	mW	
Junction temperature		T _j	100	°C	
Operating temperature range		T _{amb}	- 40 to + 85	°C	
Storage temperature range		T _{stg}	- 40 to + 100	°C	
Soldering temperature	t ≤ 5 s, 2 mm from case	T _{sd}	260	°C	
Thermal resistance junction/ambient	J-STD-051, leads 7 mm, soldered on PCB	R _{thJA}	230	K/W	





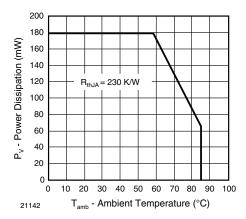


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

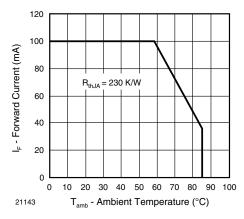


Fig. 2 - Forward Current Limit vs. Ambient Temperature

PARAMETER	CS (T _{amb} = 25 °C, unless other TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
TAHAMETER			IVIII V.			_
Forward voltage	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	V _F		1.5	1.8	V
	$I_F = 1 \text{ A}, t_p = 100 \mu s$	V_{F}		2.3		V
Temperature coefficient of V _F	I _F = 1 mA	TK _{VF}		- 1.8		mV/K
Reverse current	V _R = 5 V	I _R			10	μA
Junction capacitance	$V_R = 0 V, f = 1 MHz, E = 0$	C _j		125		pF
Radiant intensity	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	l _e	140	230	420	mW/sr
	I _F = 1 A, t _p = 100 μs	I _e		2300		mW/sr
Radiant power	$I_F = 100 \text{ mA}, t_p = 20 \text{ ms}$	фe		55		mW
Temperature coefficient of φ _e	I _F = 100 mA	TKφ _e		- 0.35		%/K
Angle of half intensity		φ		± 10		deg
Peak wavelength	I _F = 100 mA	λρ	820	850	880	nm
Spectral bandwidth	I _F = 100 mA	Δλ		40		nm
Temperature coefficient of λ_p	I _F = 100 mA	TKλ _p		0.25		nm/K
Rise time	I _F = 100 mA	t _r		20		ns
Fall time	I _F = 100 mA	t _f		13		ns
Cut-off frequency	I _{DC} = 70 mA, I _{AC} = 30 mA pp	f _c		18		MHz
Virtual source diameter		d		3.7		mm



BASIC CHARACTERISTICS (T_{amb} = 25 °C, unless otherwise specified)

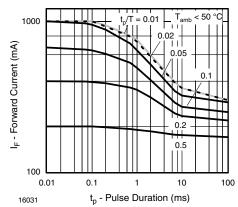


Fig. 3 - Pulse Forward Current vs. Pulse Duration

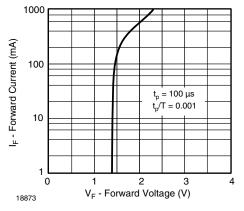


Fig. 4 - Forward Current vs. Forward Voltage

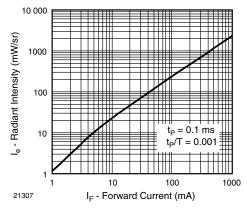


Fig. 5 - Radiant Intensity vs. Forward Current

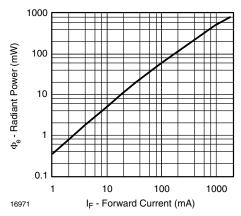


Fig. 6 - Radiant Power vs. Forward Current

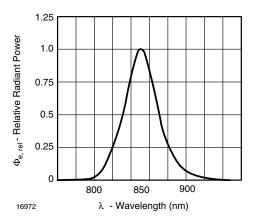


Fig. 7 - Relative Radiant Power vs. Wavelength

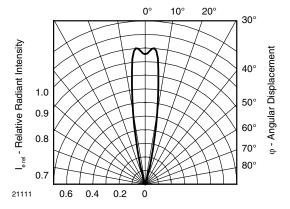
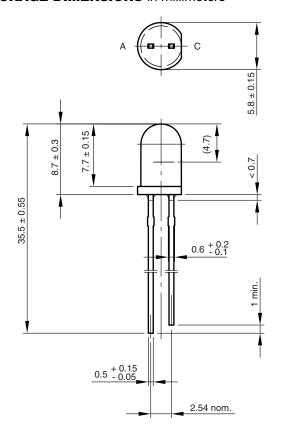
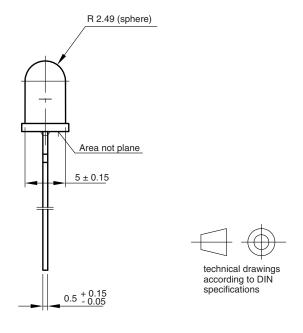


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement

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PACKAGE DIMENSIONS in millimeters





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